P-Channel Enhancement Mode Field Effect Transistor

Product Summary

● V_{DS}	-30 V
● I_D	-4.1 A
● $R_{DS(ON)}$(at V_{GS}=-10V)	43 mΩ
● $R_{DS(ON)}$(at V_{GS}=-4.5V)	65 mΩ

General Description

- Trench Power LV MOSFET technology
- High density cell design for Low RDS(ON)
- High Speed switching
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

Applications

- Battery protection
- Load switch
- Power management

■ Absolute Maximum Ratings (T_A=25 unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		V_{DS}	-30	V
Gate-source Voltage		V_{GS}	±20	V
Drain Current	T_A=25	I_D	-4.1	A
	T_A=100		-2.6	
Pulsed Drain Current [A]		I_{DM}	-30	A
Total Power Dissipation [B]	T_A=25	P_D	1.25	W
	T_A=100		0.5	

Junction and Storage Temperaran.4 reW*nBT/F5 8.07.33 0.48001 0.48

■ **Electrical Characteristics** (T_J=25 unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
[redacted] Drain-Sou[redacted]	BV_{DSS}	V_{GS}= 0V, I_D=-250μA	-30	-	-	V
Zero Gate Voltage Drain Current	[redacted]					

Typical Electrical and Thermal Characteristics Diagrams

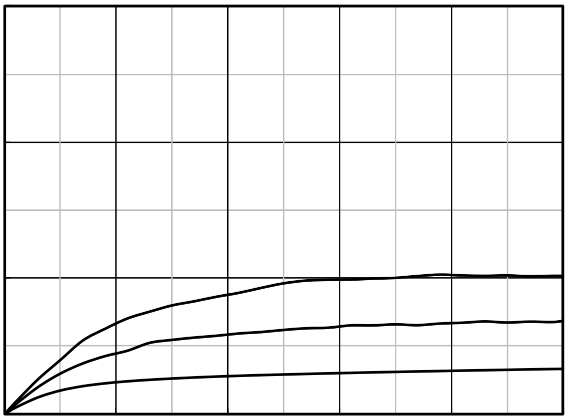


Figure 1. Output Characteristics

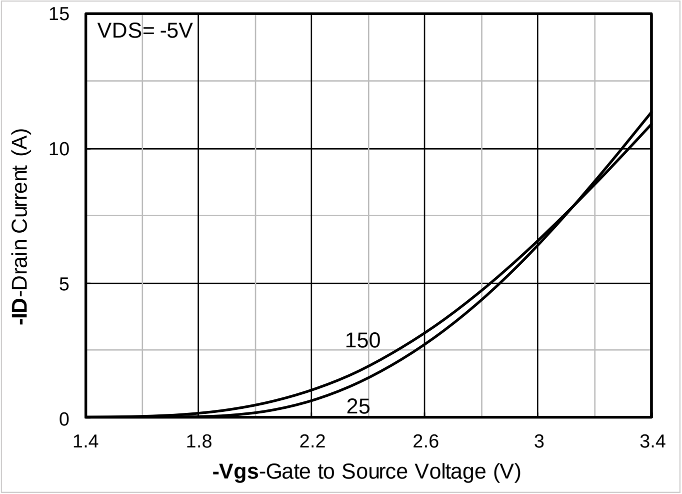


Figure 2. Transfer Characteristics

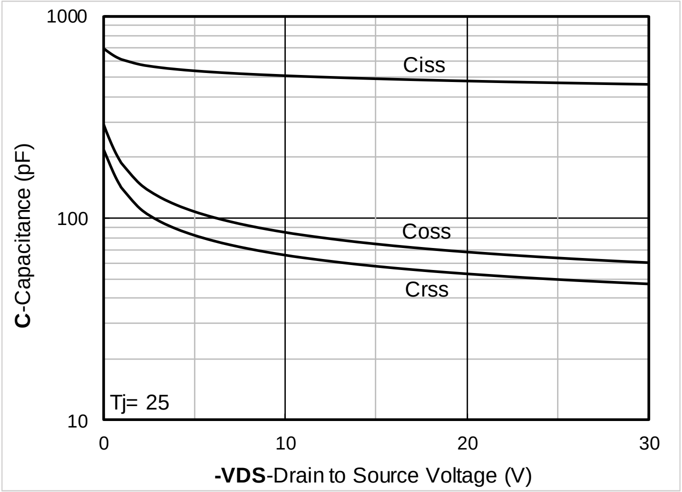


Figure 3. Capacitance Characteristics

(i)5(g)-9(ur)]TJETQq0.000008882 0 596.04 842.

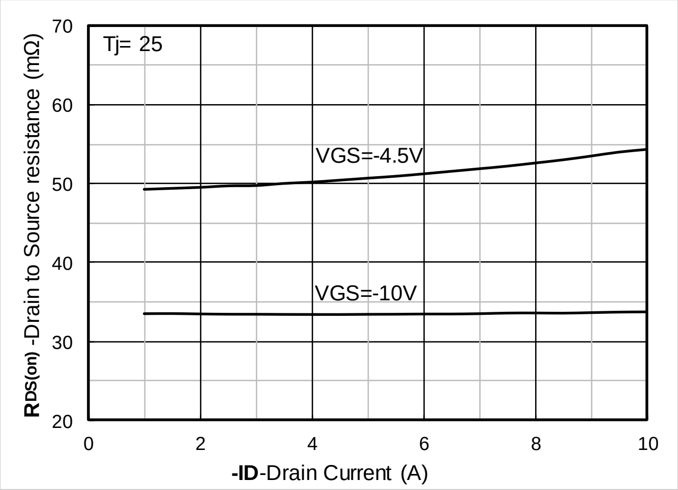


Figure 7. RDS(on) VS Drain Current

Figure 8. Forward characteristics of reverse diode

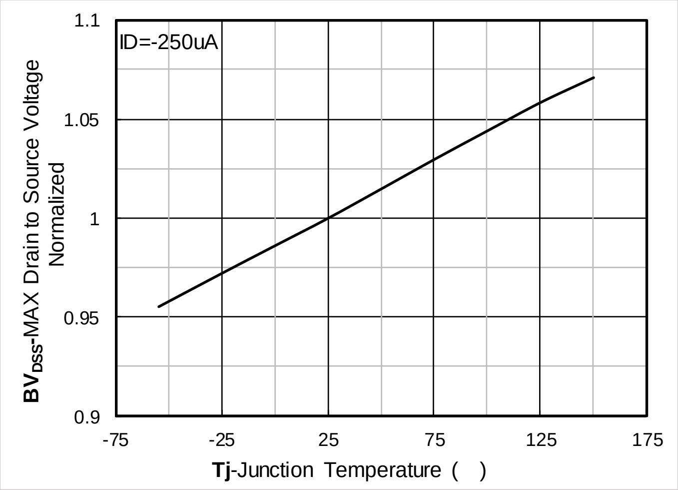


Figure 9. Normalized breakdown voltage

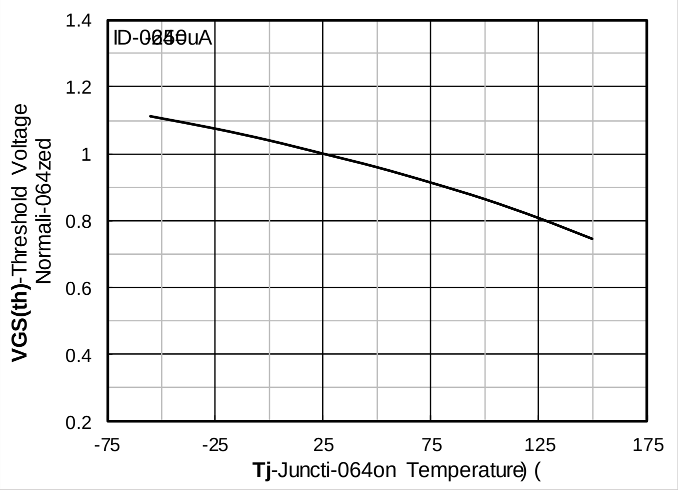


Figure 10. Normalized Threshold voltage

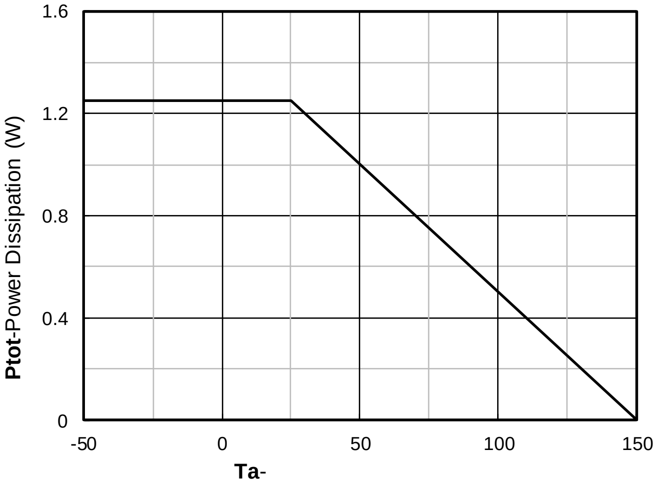
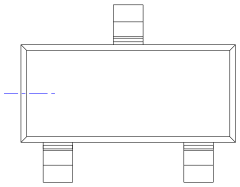
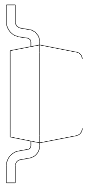


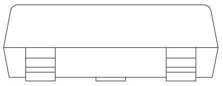
Figure 11. Current dissipation

Figure 12.

■ SOT-23 Package information







UNIT mm

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